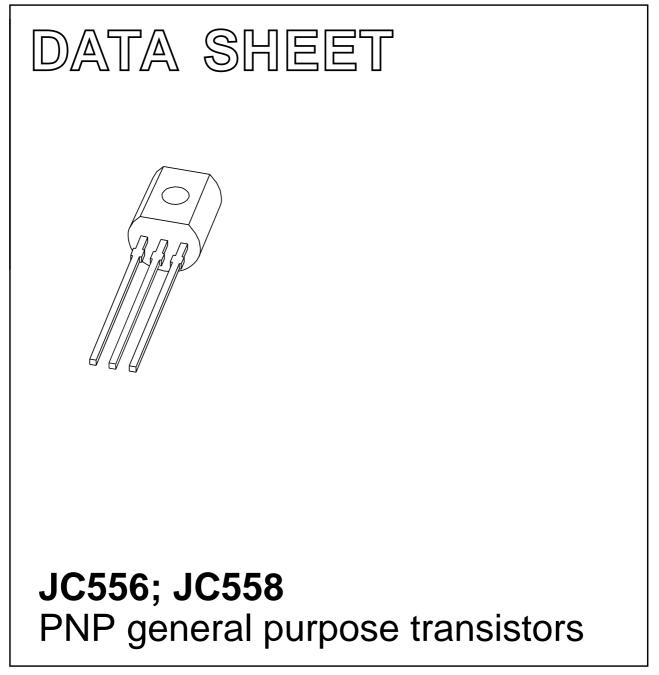
# DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1999 Apr 27 2004 Dec 08



JC556; JC558

### **PNP** general purpose transistors

#### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

### APPLICATIONS

• General purpose switching and amplification.

#### DESCRIPTION

PNP transistor in a TO-92; SOT54 plastic package. NPN complements: JC546 and JC548.

#### PINNING

PIN	DESCRIPTION	
1	base	
2	collector	
3	emitter	

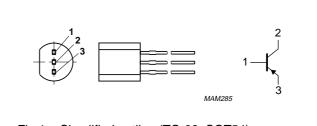


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE			
ITFE NOWBER	NAME	DESCRIPTION	VERSION		
JC556B	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54		
JC558B					

### JC556; JC558

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	JC556		_	-80	V
	JC558		_	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	JC556		_	-65	V
	JC558		_	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
I <sub>C</sub>	collector current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-200	mA
I <sub>BM</sub>	peak base current		—	-200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	250	K/W	

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

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### CHARACTERISTICS

 $T_{amb}$  = 25 °C unless otherwise specified.

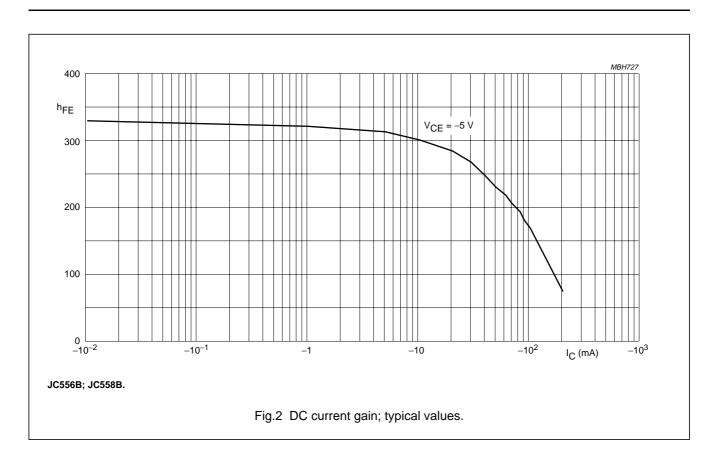
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-1	-15	nA
		$V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	_	_	-4	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	_	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_C = -2 \text{ mA}; \text{ see Fig.2}$				
	JC556B; JC558B		220	-	475	
V <sub>CEsat</sub>	collector-emitter saturation	$I_{\rm C} = -10 \text{ mA}; I_{\rm B} = -0.5 \text{ mA}$	-	-60	-300	mV
	voltage	$I_{\rm C} = -100 \text{ mA}; I_{\rm B} = -5 \text{ mA}$	-	-180	-650	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C} = -10 \text{ mA}; I_{B} = -0.5 \text{ mA}; \text{ note } 1$	-	-750	-	mV
		$I_{C} = -100 \text{ mA}; I_{B} = -5 \text{ mA}; \text{ note } 1$	-	-930	_	mV
V <sub>BE</sub>	base-emitter voltage	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}; \text{ note } 2$	-600	-650	-750	mV
		$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; \text{ note } 2$	-	-	-820	mV
C <sub>c</sub>	collector capacitance	$V_{CE} = -10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	-	4	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = -500 \text{ mV}; I_C = i_c = 0 \text{ A};$ f = 1 MHz	_	10	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; I_C = -10 \text{ mA}; f = 100 \text{ MHz}$	100	-	-	MHz
F	noise figure	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -200 \mu\text{A}; \text{ R}_{S} = 2 k\Omega;$ f = 1 kHz; B = 200 Hz	_	-	10	dB

#### Notes

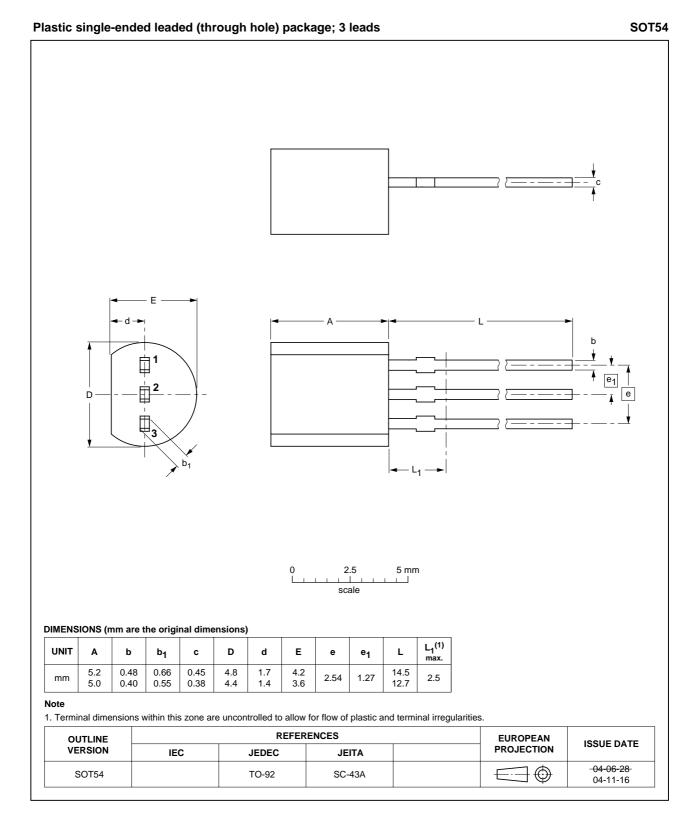
1. V<sub>BEsat</sub> decreases by about -1.7 mV/K with increasing temperature.

2.  $V_{BE}$  decreases by about –2 mV/K with increasing temperature.

### JC556; JC558



#### PACKAGE OUTLINE



JC556; JC558

JC556; JC558

#### DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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